EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	49	nitrogen with implant$5 with (interface surface) same ldd	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/04 12:50
S1	2	(("6930007") or ("20050059228")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 14:17
S2	4	(("5593907") or ("6010929") or ("6496416") or ("5877514")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:05
S3	3	(("5863828") or ("5932487") or ("6677201")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:37
S4	393034	silicon adj nitride SiN	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:38
S5	1684	(capping cap) adj layer same (anneal annealing)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:41
S6	37066	(capping cap) with (remove removing)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:41
S7	208	S4 and S5 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:49
S8	1	"20040097030"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 12:49
S9	0	("2004/0097030").URPN.	USPAT	OR	OFF	2006/03/23 13:25
S10	1	("20050059260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 14:10
S11	10	cap adj annealing and stack	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 14:12
S12	101	cap adj annealing	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 14:12
S13	4	cap adj annealing same silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/03/23 14:12

S14	496	interfacial nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 14:14
S15	104	S14 and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 14:26
S16	63217	p adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 14:27
S17	39954	lightly adj doped lld	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:28
S18	1261	nitrogen with gate adj (dielectric insulator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:29
S19	102	S16 and S17 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:35
S20	1344	nitride and (cap capping capped) same anneal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:41
S21	8	S19 and S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:35
S22	13370	nitride same (cap capping capped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:41
S23	2	S21 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 14:48

S24	2	("20050059260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/23 15:21
S25	9	BTBAS precursor nitride sidewall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 15:22
S26	17	BTBAS precursor nitride sidewall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2007/03/23 15:22
S27	75	BTBAS precursor nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 15:24
S28	16	BTBAS precursor same sidewall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 15:24
S29	40	S27 and (spacer sidewall)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 15:24
S30	63	S27 and (spacer or sidewall)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 15:51
S31	59	oxide same nitrogen with interfacial near2 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/23 15:59
S32	2	("5726087").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/23 15:59
S33	2	("20060154411").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 14:20

S34	2	dopant concentration e20 cm3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:37
S35	259	dopant concentration cm3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:38
S36	4	dopant concentration cm3 same pmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:38
S37	2	dopant concentration e20 pmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:39
S38	2	concentration e20 pmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:39
S39	3	e20 pmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:39
S40	63	e20 concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:39
S41	16	e20 concentration and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:41
S42	58	e20 and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2007/03/24 14:41
S43	2	("6576965").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:24

S44	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S45	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S46	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S47	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S48	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S49	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S50	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S51	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S52	0	("US6576965B2").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/27 12:23
S53	10	self adj aligned with lld	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 12:53

S54	16	self adj aligned same lld	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:06
S55	2561	self adj aligned same ldd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:06
S56	1415	self adj aligned with ldd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/30 13:07
S57	2	("5,061,649").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/10 13:33
S58	0	esposded with lightly adj doped adj drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 13:36
S59	0	exposded with lightly adj doped adj drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 13:36
S60	418	exposed with lightly adj doped adj drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 13:38
S61	6328	nitride near4 (cap capping)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 13:42
S62	16	S60 and S61	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 14:07
S63	532	nitrogen adj interface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 14:07

S64	4	nitrogen adj interface with (ldd lightly adj doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/10 14:07
S65	804	oxynitride with nitride with sidewall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 11:27
S66	148	S65 and (lld ldd)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 11:27
S67	0	implant%5 with nitrogen with surface same (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 11:32
S68	347	implant$5 with nitrogen with surface same (source drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 11:32
S69	806	implant$5 with nitrogen with surface and (silicon adj (oxynitride nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 11:39
S70	806	implant$5 with nitrogen with surface and (silicon adj (oxynitride nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 11:39
S71	2851	(cap capping) with (anneal annealing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 12:58
S72	28	S70 and S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 12:58
S73	11797	(cap capping) with (nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:03

S74	73	S70 and S73	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:03
S75	31158	(cap capping) with (removing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:10
S76	104493	(cap capping) with (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:19
S77	730	nitride near3 (cap capping) with (removing removed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:19
S78	3	S77 and S70	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:20
S79	4	implant$5 with nitrogen with surface and S77	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:21
S80	45	S77 and ldd and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:23
S81	244	S77 and cmos	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/14 13:27

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